

MOS FIELD EFFECT TRANSISTOR **2SK1399**

N-CHANNEL MOS FIELD EFFECT TRANSISTOR FOR HIGH SPEED SWITCHING

DESCRIPTION

The 2SK1399 is an N-channel vertical type MOS FET which can be driven by 2.5-V power supply.

The 2SK1399 is driven by low voltage and does not require consideration of driving current, it is suitable for appliances including VCR cameras and headphone stereos which need power saving.

FEATURES

- Can be driven by a 3.0-V power source
- Not necessary to consider driving current because of it is high input impedance
- Possible to reduce the number of parts by omitting the bias resistor
- Can be used complementary with the 2SJ185

ORDERING INFORMATION

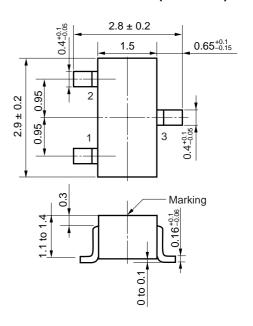
PART NUMBER	PACKAGE
2SK1399	SC-59 (Mini Mold)

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C)

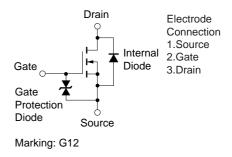
	Drain to Source Voltage	VDSS	50	V
*	Gate to Source Voltage	Vgss	±7.0	V
	Drain Current (DC)	ID(DC)	±100	mΑ
	Drain Current (pulse) Note	ID(pulse)	±200	mA
	Total Power Dissipation	Рт	200	mW
	Channel Temperature	Tch	150	°C
	Operating Temperature	Topt	-55 to +80	°C
	Storage Temperature	T_{stg}	-55 to +150	°C

Note PW \leq 10 ms, Duty Cycle \leq 50 %

PACKAGE DRAWING (Unit:mm)



EQUIVALENT CIRCUIT



Remark Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

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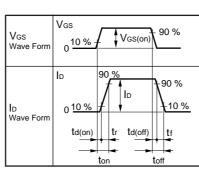
Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.



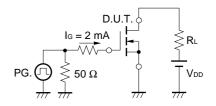
ELECTRICAL CHARACTERISTICS (TA = 25°C)

	CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
	Drain Cut-off Current	IDSS	V _{DS} = 50 V, V _{GS} = 0 V			10	μΑ
*	Gate Leakage Current	Igss	Vgs = ±7.0 V, Vps = 0 V			±5.0	μΑ
	Gate Cut-off Voltage	V _{GS(off)}	$V_{DS} = 3.0 \text{V}, I_{D} = 1.0 \mu \text{A}$	0.9	1.2	1.5	V
	Forward Transfer Admittance	y _{fs}	V _{DS} = 3.0 V, I _D = 10 mA	20	38		mS
	Drain to Source On-state Resistance	RDS(on)1	Vgs = 2.5 V, ID = 10 mA		22	40	Ω
		RDS(on)2	Vgs = 4.0 V, ID = 10 mA		14	20	Ω
	Input Capacitance	Ciss	V _{DS} = 3.0 V		8		pF
	Output Capacitance	Coss	Vgs = 0 V		7		pF
*	Reverse Transfer Capacitance	Crss	f = 1 MHz		3		pF
	Turn-on Delay Time	td(on)	V _{DD} = 3.0 V		15		ns
	Rise Time	tr	I _D = 20 mA		100		ns
	Turn-off Delay Time	td(off)	$V_{GS(on)} = 3.0 \text{ V}$		30		ns
	Fall Time	t _f	$R_G = 10 \Omega$, $R_L = 150 \Omega$		35		ns

★ TEST CIRCUIT 1 SWITCHING TIME

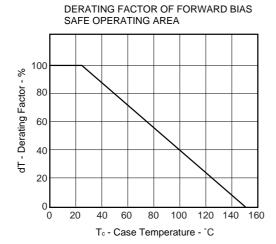


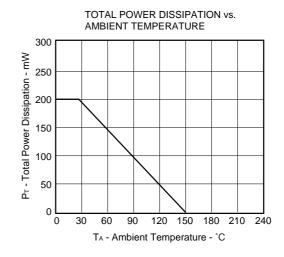
TEST CIRCUIT 2 GATE CHARGE

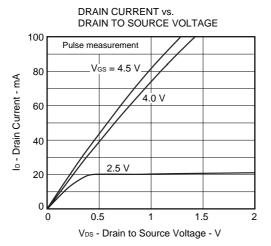


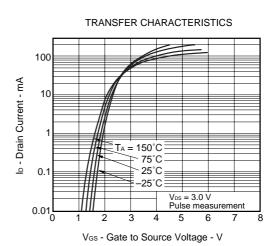


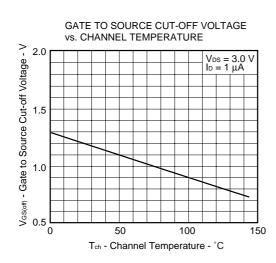
TYPICAL CHARACTERISTICS (TA = 25°C)

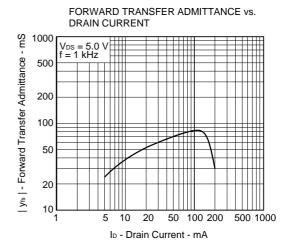




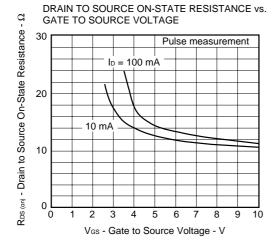


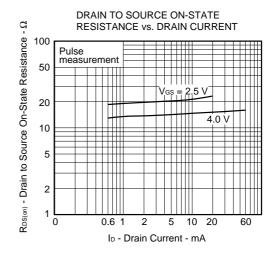






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